## A Level AQA Physics

## 29 Discrete semi-conductor devices - answers

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| Question | Answers | Extra information | Mark | AO Spec reference |
| :---: | :---: | :---: | :---: | :---: |
| 1.1 | Gate, drain, and source all correctly labelled |  | 1 | $\begin{aligned} & \text { 3.13.1.1 } \\ & \text { AO1 } \end{aligned}$ |
| 1.2 | Has very high input impedance/resistance No loading of logic gate output |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.1 } \\ & \text { AO1 } \end{aligned}$ |
| 1.3 | MOSFET can easily become charged and switch on - the resistor prevents this/ keeps gate at 0 when no input |  | 1 | $\begin{aligned} & \text { 3.13.1.1 } \\ & \text { AO1 } \end{aligned}$ |
| 1.4 | Diode <br> An induced e.m.f. is created when a motor is switched on or off Without diode this would destroy MOSFET |  | $\begin{aligned} & 1 \\ & 1 \\ & 1 \end{aligned}$ | 3.13.1.1 AO1 AO2 $\times 2$ |
| 2.1 | 2.2 V is min p.d. across gate and source to form a channel between drain and source/gate voltage when the transistor is just switched off |  | 1 | $\begin{aligned} & \text { 3.13.1.1 } \\ & \text { AO1 } \end{aligned}$ |
| 2.2 | Resistance increases as light intensity decreases <br> Potential difference across the LDR increases <br> Until threshold voltage achieved/current flows between drain and source and LED switched on |  | $\begin{aligned} & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & 3.5 .1 .5 \\ & \text { 3.13.1.1 } \\ & \text { AO2 } \end{aligned}$ |
| 2.3 | $\begin{aligned} & \text { p.d. across } R=6-2.2=3.8 \mathrm{~V} \\ & \frac{R}{3.8}=\frac{100000}{2.2} \\ & R=100000 \times \frac{3.8}{2.2} \\ & R=170 \mathrm{k} \Omega \end{aligned}$ |  | $\begin{aligned} & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & 3.5 .1 .5 \\ & \text { 3.13.1.1 } \\ & \text { AO2 } \end{aligned}$ |

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| 3.1 | Max 4 marks from: <br> - Behaviour in forward bias direction same/same threshold voltage and then low resistance <br> - Diode has large breakdown voltage/zener diodes have low breakdown voltages <br> - Diode breaks if breakdown voltage exceeded/voltage across zener/zener voltage remains constant even when current exceeded <br> - Reverse current of zener remains constant/at least 5 mA until breakdown voltage applied | Must have similarities and differences for full marks | max 4 | $\begin{aligned} & \text { 3.13.1.2 } \\ & \text { AO2 } \end{aligned}$ |
| 3.2 | Correct symbol drawn Arrow pointing up |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.2 } \\ & \text { AO1 } \end{aligned}$ |
| 3.3 | $\begin{aligned} P & =V I \\ I & =\frac{P}{V}=\frac{1.3}{4.3}=0.30 \mathrm{~A} \end{aligned}$ |  | 1 | 3.5.1.4 3.13.1.2 AO1 |
| 3.4 | $\begin{aligned} & V=9-4.3=4.7 \mathrm{~V} \\ & V=I R \\ & R=\frac{4.7}{0.3}=16 \Omega \end{aligned}$ |  | 1 <br> 1 | $\begin{aligned} & \text { 3.5.1.1 } \\ & 3.13 .1 .2 \\ & \text { AO2 } \end{aligned}$ |
| 4.1 | In parallel with zener diode so $\mathrm{pd}=4.7 \mathrm{~V}$ $I=\frac{V}{R}=\frac{4.7}{440}=0.011 \mathrm{~A}$ |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.2 } \\ & 3.5 .1 .1 \\ & \text { AO2 } \end{aligned}$ |
| 4.2 | $\begin{aligned} & \text { p.d. }=10-4.7=5.3 \mathrm{~V} \\ & I=\frac{V}{R}=\frac{5.3}{120}=0.044 \mathrm{~A} \end{aligned}$ |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.2 } \\ & 3.5 .1 .1 \\ & \text { AO2 } \end{aligned}$ |
| 4.3 | $I_{\mathrm{Z}}=0.044-0.011=0.033 \mathrm{~A}$ |  | 1 | $\begin{aligned} & \text { 3.13.1.2 } \\ & \text { 3.5.1.4 } \\ & \text { AO1 } \end{aligned}$ |

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| 4.4 | $P=I V=0.033 \mathrm{~A} \times 4.7=0.16 \mathrm{~W}<0.25 \mathrm{~W}$ <br> Use 250 mW zener diode |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.2 } \\ & 3.5 .1 .4 \\ & \text { AO2 } \end{aligned}$ |
| 5.1 | Reverse |  | 1 | $\begin{aligned} & \text { 3.13.1.3 } \\ & \text { AO1 } \end{aligned}$ |
| 5.2 | Inverted parabola <br> Peak at 850 nm <br> Scale from 550 nm (min) to 1150 nm (max) | Ignore $y$-axis scale | $\begin{aligned} & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.3 } \\ & \text { AO1 } \end{aligned}$ |
| 5.3 | $\begin{aligned} & \text { Power }=I \times \text { Area }=10 \times 1 \times 10^{-6} \mathrm{~m}^{2} \\ & \text { Current }=\text { sensitivity } \times \text { power }=0.62 \times 10 \times 1 \times 10^{-6} \\ & \text { Current }=6.2 \times 10^{-6} \mathrm{~A} \end{aligned}$ |  | $\begin{aligned} & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.3 } \\ & \text { 3.5.1.4 } \\ & \text { AO3 } \end{aligned}$ |
| 5.4 | Max 4 marks from: <br> - Photodiode in series with a resistor and a power supply <br> - $V_{\text {out }}$ across the resistor <br> - When it is dark, the current is negligible and there is no pd across resistor. No $V_{\text {out }}$ <br> - When it is light, there is a current and hence a pd across the resistor - this is $V_{\text {out }}$ <br> - Resistor chosen to provide suitable pd to activate alarm | All marks can be awarded for suitably labelled diagram | $\max 4$ | $\begin{aligned} & 3.13 .1 .3 \\ & \text { AO3 } \end{aligned}$ |
| 6.1 | Magnet placed on frame of set in line with hall effect sensor (allow vice versa) When the magnet is close to the sensor, voltage output is high/far from it, voltage output low <br> Output fed to circuits for airbags/output amplified and input to circuits for airbags |  | $\begin{aligned} & 1 \\ & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & 3.13 .1 .4 \\ & \text { AO1 } \end{aligned}$ |
| 6.2 | $\begin{aligned} & 3.5 \times 10^{-4} \mathrm{~T}=0.35 \mathrm{mT} \\ & V=9 \times 0.35=3.2 \mathrm{mV} \\ & 0.014 \mathrm{~T}=14 \mathrm{mT} \\ & V=9 \times 14=126 \mathrm{mV} \end{aligned}$ |  | $1$ <br> 1 | $\begin{aligned} & 3.13 .1 .4 \\ & \text { AO2 } \end{aligned}$ |

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| 6.3 | $\begin{aligned} & 0.065 \mathrm{mT} \\ & V=0.59 \mathrm{mV} \end{aligned}$ <br> Too small to affect reading as this was max strength $20 \%$ of smallest value so would affect accuracy of output |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.4 } \\ & \text { AO2 } \end{aligned}$ |
| 7.1 | As the magnet passes the sensor, it registers a voltage output The number of voltage outputs can be counted Using circumference of wheel, the distance can be measured/number of counts multiplied by distance of wheel |  | $1$ <br> 1 <br> 1 | $\begin{aligned} & \text { 3.13.1.4 } \\ & \text { AO3 } \end{aligned}$ |
| 7.2 | $\begin{aligned} & \text { Distance }=\pi \times D=\pi \times 0.05 \mathrm{~m} \\ & \text { Speed }=\frac{\text { distance }}{\text { time }}=\frac{\pi \times 0.05 \mathrm{~m}}{6.5 \times 10^{-3}}=24 \mathrm{~m} \mathrm{~s}^{-1} \end{aligned}$ |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & \text { 3.13.1.4 } \\ & \text { AO2 } \end{aligned}$ |
| 7.3 | Have more magnets on disc/have a smaller radius disc | Allow any sensible suggestion here | 1 | $\begin{aligned} & \text { 3.13.1.4 } \\ & \text { AO3 } \end{aligned}$ |
| 8.1 | Reverse |  | 1 | $\begin{aligned} & \text { 3.13.1.3 } \\ & \text { AO1 } \end{aligned}$ |
| 8.2 | Leakage current when there is no/zero light intensity |  | 1 | $\begin{aligned} & \text { 3.13.1.3 } \\ & \text { AO1 } \end{aligned}$ |
| 8.3 | $\begin{aligned} & \text { Current }=0.6 \mathrm{AW}^{-1} \times 0.2 \times 10^{-3} \mathrm{~W} \\ & \text { Current }=1.2 \times 10^{-4} \mathrm{~A} \end{aligned}$ |  | 1 | $\begin{aligned} & 3.13 .1 .3 \\ & 3.5 .1 .4 \\ & \text { AO2 } \end{aligned}$ |
| 8.4 | $\begin{aligned} & \text { p.d. across } R=I R=1.2 \times 10^{-4} \mathrm{~A} \times 5000 \Omega=0.6 \mathrm{~V} \\ & V_{\text {out }}=9.0-0.6=8.4 \mathrm{~V} \end{aligned}$ |  | $\begin{aligned} & 1 \\ & 1 \end{aligned}$ | $\begin{aligned} & 3.13 .1 .3 \\ & 3.5 .1 .1,3.5 .1 .4 \\ & \text { AO2 } \end{aligned}$ |

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Skills box answers

| Question | $\quad$ Answer |
| :--- | :--- |
| $\mathbf{1}$ | $I_{\max }=\frac{P}{V}=\frac{500 \times 10^{-3} \mathrm{~W}}{5.1 \mathrm{~V}}=0.10 \mathrm{~A}$ |
| $\mathbf{2}$ | $P=I V=10 \times 10^{-3} \mathrm{~A} \times 2.7 \mathrm{~V}=0.03 \mathrm{~W}$ |
| $\mathbf{3}$ | $R_{\min }=\frac{\left(V_{\mathrm{s}}-V_{z}\right)}{I_{\max }}=\frac{(12-10) \mathrm{V}}{100 \times 10^{-3} \mathrm{~A}}=20 \Omega$ |

